

INTEGRATED CIRCUIT WITH PROTECTIVE MOAT

ABSTRACT

A method of manufacturing an integrated circuit provides a substrate having a semiconductor device, and includes forming an intermetal dielectric layer over the substrate and the semiconductor device. A metal wire is formed above the semiconductor device and in contact therewith and a passivation layer is formed over the intermetal dielectric layer. A bond pad is formed connected to the metal wire. A protective moat is formed through the passivation layer and the intermetal dielectric layer, and is located between the metal wire and an outside edge of the integrated circuit.

FIG. 3